Claims

| [c1] | A thick film heater comprising a target object to be heated, wherein said target object is located in an environment of ambient temperatures significantly below 0 ° C; a heating element consisting of an electrically thick film resistive circuit applied directly to a surface of said target object; and wherein said electrically thick film resistive circuit is polymer based. |
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| [c2] | The thick film heater of claim 1 wherein said target object is designed to operate at temperatures below -75 ° C. |
| [c3] | The thick film heater of claim 2 wherein said target object is designed to operate at temperatures below -150° C. |
| [c4] | The thick film heater of claim 1 wherein said heating element is capable of heat flux at least as great as 200 watts per square inch. |
| [c5] | The thick film heater of claim 1 wherein said target object is non-ferrous. |
| [c6] | The thick film heater of claim 5 wherein said target object is aluminum. |
| [c7] | The thick film heater of claim 5 wherein said target object is copper. |
| [c8] | The thick film heater of claim 5 wherein said target object is ceramic. |
| [c9] | The thick film heater of claim 1 wherein said target object is a high-expansion steel. |
| [c10] | The thick film heater of claim 1 wherein said heating element further comprises a dielectric layer disposed between said target object and said electrically resistive circuit. |
| [c11] | The thick film heater of claim 10 wherein said heating element further comprises a second dielectric layer disposed over said electrically resistive circuit, away from said target object. |
| [c12] | The thick film heater of claim 10 wherein said dielectric layer consists of a |

[c16]

[c13] The thick film heater of claim 12 wherein said metal oxide is selected from the group consisting of TiO2, SiO2, and Al2O3.
 [c14] A method of manufacturing a thick film heater comprising a heating element

metal oxide.

[c14] A method of manufacturing a thick film heater comprising a heating element applied directly to a surface of a target object, the method comprising the steps of:

applying the heating element, comprising a thick film resistive circuit directly to the surface of the target object, wherein the thick film resistive circuit is made of a polymer-based ink; curing the heating element at a temperature in excess of 150 ° C for a period of time in excess of thirty minutes; and sealing the heating element with a dielectric layer.

[c15] The method of claim 14 further comprising a plurality of said curing steps, wherein at least one of said curing steps occurs at a temperature in excess of 150 ° C for a period of time in excess of thirty minutes.

The method of claim 14 further comprising the step of preparing the surface of the target object with a lower dielectric layer, and wherein the heating element in said applying layer is applied over the lower dielectric layer.

[c17] The method of claim 14 wherein said curing step occurs at a temperature of 200 ° C or greater.

[c18] The method of claim 14 wherein said curing step occurs for a period of two hours or longer.

[c19] The method of claim 14 wherein the heating element is designed to operate at greater than 15 W/cm 2 .

[c20] The method of claim 14 wherein the target object is non-ferrous.

[c21] The method of claim 20 wherein the target object is aluminum.

[c22] The method of claim 19 wherein the target object is copper.

| [c23] | The method of claim 20 wherein the target object is ceramic. |
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| [c24] | The method of claim 13 wherein the target object is high-expansion steel. |
| [c25] | The method of claim 13 wherein the polymer base of the thick film resistive circuit is an epoxy. |
| [c26] | The method of claim 24 wherein the polymer-based ink contains silver particles. |